# Noninverting Buffer / CMOS Logic Level Shifter

with LSTTL-Compatible Inputs

The MC74VHC1GT126 is a single gate noninverting 3–state buffer fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The MC74VHC1GT126 requires the 3-state control input (OE) to be set Low to place the output into the high impedance state.

The device input is compatible with TTL-type input thresholds and the output has a full 5 V CMOS level output swing. The input protection circuitry on this device allows overvoltage tolerance on the input, allowing the device to be used as a logic-level translator from 3 V CMOS logic to 5 V CMOS Logic or from 1.8 V CMOS logic to 3 V CMOS Logic while operating at the high-voltage power supply.

The MC74VHC1GT126 input structure provides protection when voltages up to 7 V are applied, regardless of the supply voltage. This allows the MC74VHC1GT126 to be used to interface 5 V circuits to 3 V circuits. The output structures also provide protection when  $V_{CC}=0$  V. These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

#### **Features**

- High Speed:  $t_{PD} = 3.5 \text{ ns}$  (Typ) at  $V_{CC} = 5 \text{ V}$
- Low Power Dissipation:  $I_{CC} = 1 \mu A \text{ (Max)}$  at  $T_A = 25 \text{°C}$
- TTL-Compatible Inputs:  $V_{IL} = 0.8 \text{ V}$ ;  $V_{IH} = 2 \text{ V}$
- CMOS–Compatible Outputs:  $V_{OH} > 0.8 V_{CC}$ ;  $V_{OL} < 0.1 V_{CC}$  @Load
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Pin and Function Compatible with Other Standard Logic Families
- Chip Complexity: FETs = 62; Equivalent Gates = 16
- Pb-Free Packages are Available

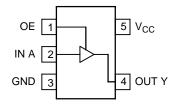


Figure 1. Pinout (Top View)



Figure 2. Logic Symbol



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MARKING DIAGRAMS







**CASE 483** 



W3 = Device Code

M = Date Code\*

= Pb-Free Package

(Note: Microdot may be in either location)\*Date Code orientation and/or position may vary depending upon manufacturing location.

	PIN ASSIGNMENT				
	1	OE			
	2	IN A			
Γ	3	GND			
	4	OUT Y			
Γ	5	V <sub>CC</sub>			

#### **FUNCTION TABLE**

A Input	OE Input	Y Output
L	Н	L
Н	Н	Н
X	L	Z

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

#### **MAXIMUM RATINGS**

Symbol	Characteristics	Value	Unit
V <sub>CC</sub>	DC Supply Voltage	-0.5 to +7.0	V
V <sub>IN</sub>	DC Input Voltage	-0.5 to +7.0	V
V <sub>OUT</sub>	DC Output Voltage	–0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input Diode Current	-20	mA
I <sub>OK</sub>	Output Diode Current $V_{OUT} < GND; V_{OUT} > V_{CC}$	+20	mA
I <sub>OUT</sub>	DC Output Current, per Pin	+25	mA
I <sub>CC</sub>	DC Supply Current, V <sub>CC</sub> and GND	+50	mA
$P_{D}$	Power Dissipation in Still Air SC–88A, TSOP–5	200	mW
$\theta_{JA}$	Thermal Resistance SC-88A, TSOP-5	333	°C/W
TL	Lead Temperature, 1 mm from Case for 10 s	260	°C
TJ	Junction Temperature Under Bias	+150	°C
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
V <sub>ESD</sub>	ESD Withstand Voltage  Human Body Model (Note 1)  Machine Model (Note 2)  Charged Device Model (Note 3)	> 2000 > 200 N/A	V
I <sub>Latchup</sub>	Latchup Performance Above V <sub>CC</sub> and Below GND at 125°C (Note 4)	±500	mA

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- 1. Tested to EIA/JESD22-A114-A
- 2. Tested to EIA/JESD22-A115-A
- 3. Tested to JESD22-C101-A
- 4. Tested to EIA/JESD78

#### RECOMMENDED OPERATING CONDITIONS

Symbol	Characteristics	Min	Max	Unit	
V <sub>CC</sub>	DC Supply Voltage	3.0	5.5	V	
V <sub>IN</sub>	DC Input Voltage	0.0	5.5	V	
V <sub>OUT</sub>	DC Output Voltage	0.0	V <sub>CC</sub>	V	
T <sub>A</sub>	Operating Temperature Range			+125	°C
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time V <sub>CC</sub> = 5.0	V ± 0.5 V	0	20	ns/V

#### Device Junction Temperature versus Time to 0.1% Bond Failures

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

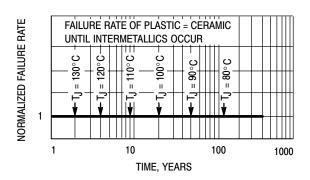


Figure 3. Failure Rate vs. Time Junction Temperature

#### DC ELECTRICAL CHARACTERISTICS

			Vcc	T <sub>A</sub> = 25°C		T <sub>A</sub> ≤	85°C	-55 ≤ T <sub>4</sub>	√ ≤ 125°C		
Symbol	Parameter	Test Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Unit
V <sub>IH</sub>	Minimum High-Level Input Voltage		3.0 4.5 5.5	1.4 2.0 2.0			1.4 2.0 2.0		1.4 2.0 2.0		V
V <sub>IL</sub>	Maximum Low-Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
V <sub>OH</sub>	Minimum High-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OH} = -50 \mu A$	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
	$V_{IN} = V_{IH}$ or $V_{IL}$	$V_{IN} = V_{IH}$ or $V_{IL}$ $I_{OH} = -4$ mA $I_{OH} = -8$ mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		
V <sub>OL</sub>	Maximum Low-Level Output Voltage	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 50  \mu\text{A}$	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
	$V_{IN} = V_{IH}$ or $V_{IL}$	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $I_{OL} = 4 \text{ mA}$ $I_{OL} = 8 \text{ mA}$	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	
I <sub>IN</sub>	Maximum Input Leak- age Current	V <sub>IN</sub> = 5.5 V or GND	0 to 5.5			± 0.1		± 1.0		± 1.0	μΑ
I <sub>CC</sub>	Maximum Quiescent Supply Current	$V_{IN} = V_{CC}$ or GND	5.5			1.0		20		40	μΑ
I <sub>CCT</sub>	Quiescent Supply Current	Input: V <sub>IN</sub> = 3.4 V Other Input: V <sub>CC</sub> or GND	5.5			1.35		1.50		1.65	mA
I <sub>OPD</sub>	Output Leakage Current	V <sub>OUT</sub> = 5.5 V	0.0			0.5		5.0		10	μΑ
l <sub>OZ</sub>	Maximum 3–State Leakage Current	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$	5.5			± 0.25		± 2.5		± 2.5	μΑ

### AC ELECTRICAL CHARACTERISTICS Input $t_f = t_f = 3.0 \text{ ns}$

Power Dissipation Capacitance (Note 5)

			T <sub>A</sub> = 25°C		С	T <sub>A</sub> ≤	85°C	-55 ≤ T <sub>A</sub>	≤ 125°C	
Symbol	Parameter	Test Conditions	Min	Тур	Max	Min	Max	Min	Max	Unit
t <sub>PLH</sub> , t <sub>PHL</sub>	Maximum Propagation Delay, A to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15p$ $C_L = 50p$		5.6 8.1	8.0 11.5	1.0 1.0	9.5 13.0		12.0 16.0	ns
	(Figures 3 and 5)	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 15p$ $C_L = 50p$		3.8 5.3	5.5 7.5	1.0 1.0	6.5 8.5		8.5 10.5	
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Output Enable TIme, OE to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15p$ $R_L = R_I = 500 \Omega$ $C_L = 50p$		5.4 7.9	8.0 11.5	1.0 1.0	9.5 13.0		11.5 15.0	ns
	(Figures 4 and 5)	$\begin{array}{cccccccccccccccccccccccccccccccccccc$		3.6 5.1	5.1 7.1	1.0 1.0	6.0 8.0		7.5 9.5	
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Output Disable Time, OE to Y	$V_{CC} = 3.3 \pm 0.3 \text{ V}$ $C_L = 15 \text{p}$ $R_L = R_I = 500 \Omega$ $C_L = 50 \text{p}$		6.5 8.0	9.7 13.2	1.0 1.0	11.5 15.0		14.5 18.0	ns
	(Figures 4 and 5)	$V_{CC} = 5.0 \pm 0.5 \text{ V}$ $C_L = 15p$ $R_L = R_I = 500 \Omega$ $C_L = 50p$		4.8 7.0	6.8 8.8	1.0 1.0	8.0 10.0		10.0 12.0	
C <sub>in</sub>	Maximum Input Capacitance			4	10		10		10	pF
C <sub>out</sub>	Maximum Three–State Output Capacitance (Output in High Impedance State)			6						pF
					Тур	oical @	25°C, \	/ <sub>CC</sub> = 5.0 \	/	

5. C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I<sub>CC(OPR)</sub> = C<sub>PD</sub> • V<sub>CC</sub> • f<sub>in</sub> + I<sub>CC</sub>/4 (per buffer). C<sub>PD</sub> is used to determine the no–load dynamic power consumption; P<sub>D</sub> = C<sub>PD</sub> • V<sub>CC</sub><sup>2</sup> • f<sub>in</sub> + I<sub>CC</sub> • V<sub>CC</sub>.

#### **SWITCHING WAVEFORMS**

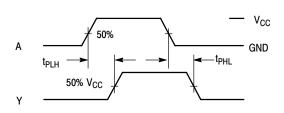
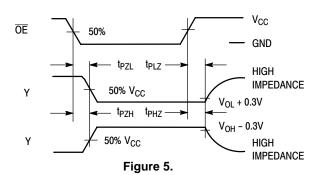
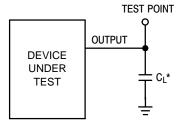
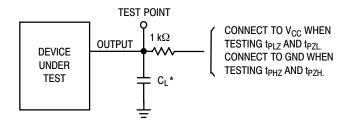


Figure 4. Switching Waveforms





\*Includes all probe and jig capacitance



\*Includes all probe and jig capacitance

Figure 6. Test Circuit

Figure 7. Test Circuit

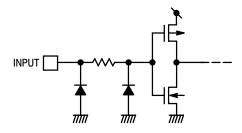


Figure 8. Input Equivalent Circuit

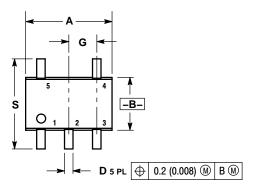
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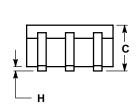
Device	Package	Shipping <sup>†</sup>
MC74VHC1GT126DF1	SC-88A / SOT-353 / SC-70	
M74VHC1GT126DF1G	SC-88A / SOT-353 / SC-70 (Pb-Free)	
MC74VHC1GT126DF2	SC-88A / SOT-353 / SC-70	
M74VHC1GT126DF2G	SC-88A / SOT-353 / SC-70 (Pb-Free)	3000 / Tape & Reel
MC74VHC1GT126DT1	TSOP-5 / SOT-23 / SC-59	
M74VHC1GT126DT1G	TSOP-5 / SOT-23 / SC-59 (Pb-Free)	

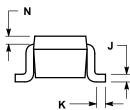
<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

#### **PACKAGE DIMENSIONS**

SC-88A, SOT-353, SC-70 CASE 419A-02 **ISSUE J** 



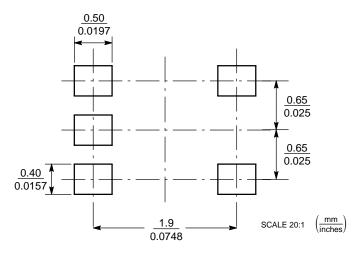




- NOTES:
  1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. 419A-01 OBSOLETE. NEW STANDARD 419A-02.
  4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	INC	HES	MILLIN	IETERS	
DIM	MIN	MAX	MIN	MAX	
Α	0.071	0.087	1.80	2.20	
В	0.045	0.053	1.15	1.35	
С	0.031	0.043	0.80	1.10	
D	0.004	0.012	0.10	0.30	
G	0.026	BSC	0.65 BSC		
Н		0.004		0.10	
J	0.004	0.010	0.10	0.25	
K	0.004	0.012	0.10	0.30	
N	N 0.008 REF		0.20	REF	
S	0.079	0.087	2.00	2.20	

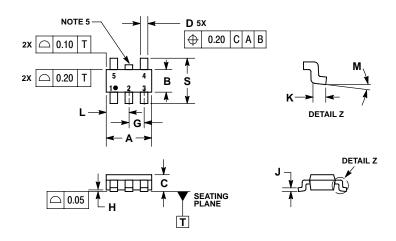
#### **SOLDERING FOOTPRINT\***



\*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

#### PACKAGE DIMENSIONS

TSOP-5 CASE 483-02 ISSUE F



#### NOTES:

- ASTES.

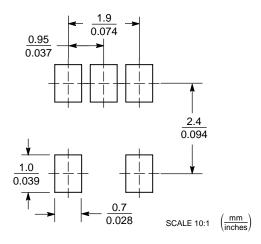
  1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.

  2. CONTROLLING DIMENSION: MILLIMETERS.
- CONTROLLING DIMENSION: MILLIMETERS
   MAXIMUM LEAD THICKNESS INCLUDES
   LEAD FINISH THICKNESS. MINIMUM LEAD
   THICKNESS IS THE MINIMUM THICKNESS
- OF BASE MATERIAL.

  4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE
- BURRS.
  5. OPTIONAL CONSTRUCTION: AN
  ADDITIONAL TRIMMED LEAD IS ALLOWED
  IN THIS LOCATION. TRIMMED LEAD NOT TO
  EXTEND MORE THAN 0.2 FROM BODY.

	MILLIMETERS					
DIM	MIN	MAX				
Α	3.00	BSC				
В	1.50	BSC				
C	0.90	1.10				
D	0.25	0.50				
G	0.95	BSC				
Н	0.01	0.10				
7	0.10	0.26				
K	0.20	0.60				
L	1.25	1.55				
М	0 °	0° 10°				
S	2.50	3.00				

#### **SOLDERING FOOTPRINT\***



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